Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- · High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- · Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Isolated package

3. Applications

- · General purpose motor control
- · General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{DRM}	repetitive peak off-state voltage			8	00		V
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 73 °C; Fig. 1; Fig. 2; Fig. 3	8		А		
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	65		А		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$		-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	30	70	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		Ν
3	G	gate		T2 T1
mb	n.c.	mounting base; isolated		sym051

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
BT137X-800	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Marking

Table 4. Marking codes

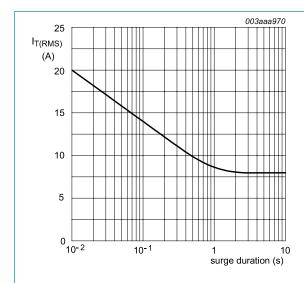
Type number	Marking codes
BT137X-800	BT137X-800

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Values	Unit
repetitive peak off-state voltage		800	V
RMS on-state current	full sine wave; T _h ≤ 73 °C; Fig 1; Fig 2; Fig 3	8	А
non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	65	Α
	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	71	А
I ² t for fusing	t _p = 10 ms; SIN	21	A ² s
rate of rise of on-state current	I _G = 70 mA; T2+ G+	50	A/µs
	I _G = 70 mA; T2+ G-	50	A/µs
	I _G = 70 mA; T2- G-	50	A/µs
	I _G = 140 mA; T2- G+	10	A/µs
peak gate current		2	А
peak gate power		5	W
average gate power	over any 20 ms period	0.5	W
storage temperature		-40 to 150	°C
junction temperature		125	°C
	repetitive peak off-state voltage RMS on-state current non-repetitive peak on-state current I²t for fusing rate of rise of on-state current peak gate current peak gate power average gate power storage temperature	repetitive peak off-state voltage RMS on-state current full sine wave; $T_h \le 73$ °C; Fig 1; Fig 2; Fig 3 non-repetitive peak onstate current full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5 full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms $I^2t \text{ for fusing} \qquad t_p = 10 \text{ ms; SIN}$ rate of rise of on-state current $I_G = 70 \text{ mA; T2+ G-}$ $I_G = 70 \text{ mA; T2- G-}$ $I_G = 140 \text{ mA; T2- G-}$ peak gate current peak gate power average gate power average gate power storage temperature	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$



f = 50 Hz; T_h = 73 °C Fig. 1. RMS on-state current as a function of surge duration; maximum values

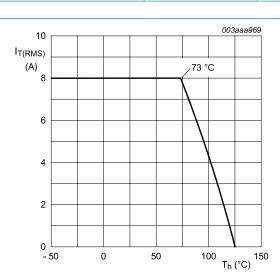
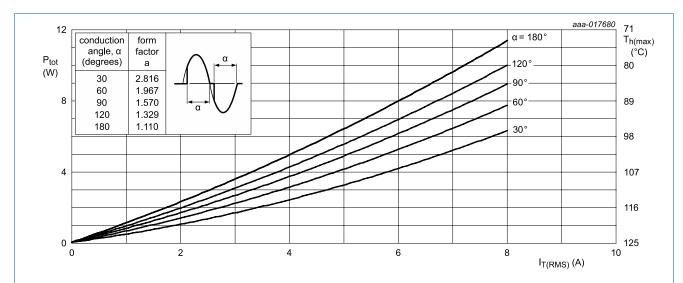


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

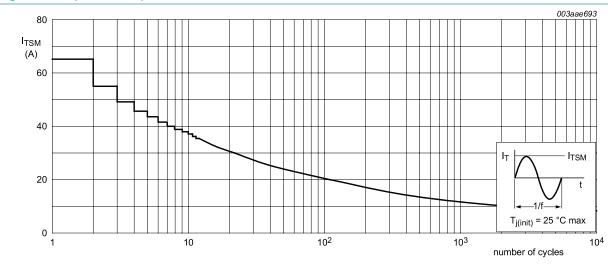
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 α = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

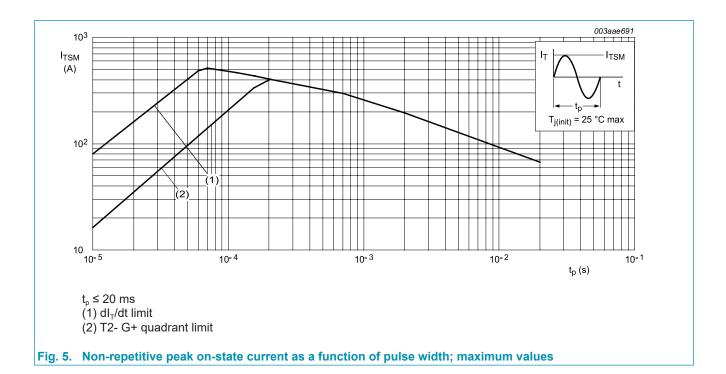
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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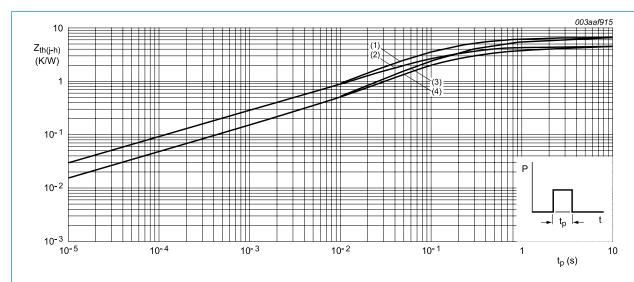


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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig 6	-	-	4.5	K/W
	heatsink	full or half cycle; without heatsink compound; Fig 6	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

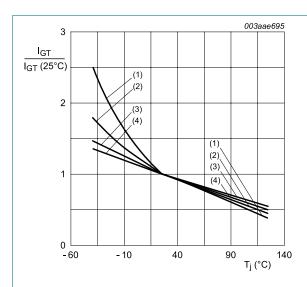
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; $T_h = 25$ °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

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11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	30	70	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	5	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	7	45	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	5	20	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_{j} = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 \text{ °C}; I_T = 8 \text{ A};$ $dI_{com}/dt = 3.6 \text{ A/ms}$	-	20	-	V/µs
t _{gt}	gate-controlled turn-on time	$V_D = 800 \text{ V}; I_{TM} = 12 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

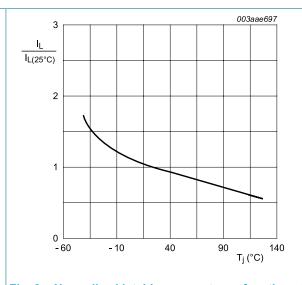


Fig. 8. Normalized latching current as a function of junction temperature

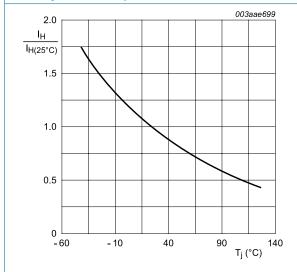
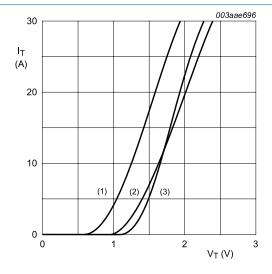


Fig. 9. Normalized holding current as a function of junction temperature



- V_o = 1.264 V; R_s = 0.038 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values
- (3) $T_i = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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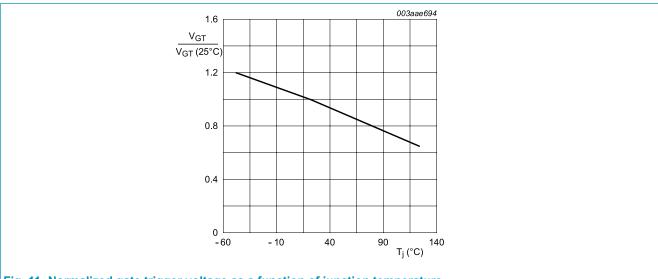
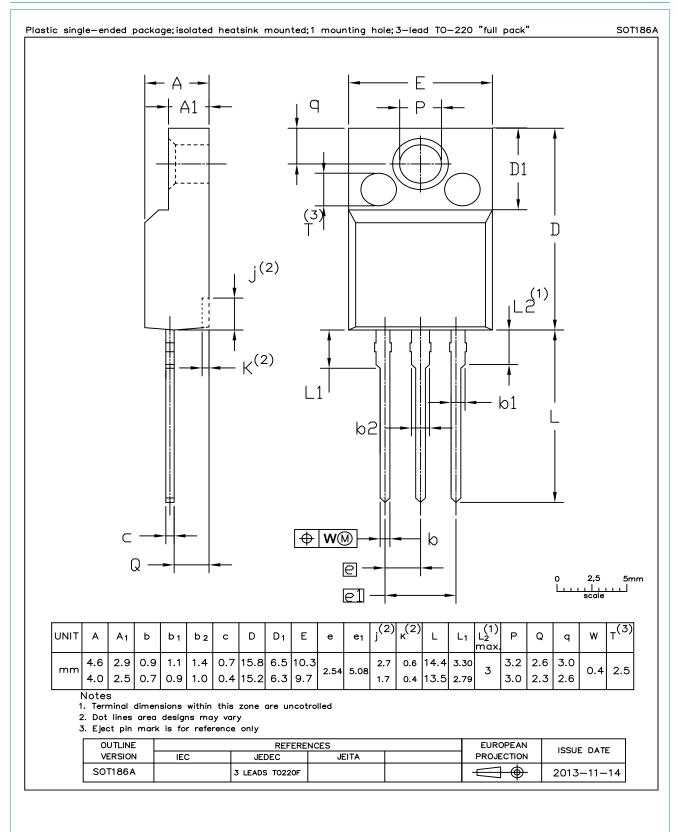


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.ween-semi.com
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